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PTO/SB/08A (08-00)

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Complete if Known

Application Number	09/904,906
Filing Date	July 16, 2001
First Named Inventor	Takeshi FUKADA et al.
Group Art Unit	2825
Examiner Name	L. Malsawma
Attorney Docket Number	0756-2332

Sheet

1

of

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U.S. PATENT DOCUMENTS

Examiner Initials [*]	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
AM		4,416,952		Nishizawa et al.	11/22/1983	
		4,727,044		Yamazaki	02/23/1988	
		5,147,826		Liu et al.	09/15/1992	
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Examiner Initials [*]	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁴
		Office ²	Number ³	Kind Code ² (if known)				
AM		JP	01-144139			06/06/1989		AB
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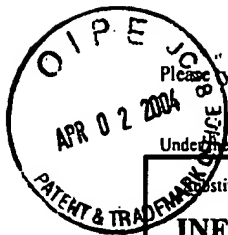
Examiner Signature	Mail J. Lee L. Malsawma	Date Considered	6/12/04
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¹ Unique citation designation number. ² Applicant is to place a check mark here if English language Translation is attached.

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Sheet	2	of	2	Attorney Docket Number	0756-2332

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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
Alm		Gang Liu et al., <i>Polycrystalline Silicon Thin Film Transistors on Corning 7059 Glass Substrates Using Short Time, Low-Temperature Processing</i> , Appl. Phys. Lett., Vol. 62, No. 20, Pages 2554-2556, May 17, 1993.	
Alm		Gang Liu et al., <i>Selective Area Crystallization of Amorphous Silicon Films by Low-Temperature Rapid Thermal Annealing</i> , Appl. Phys. Lett., Vol. 55, No. 7, Pages 660-662, August 14, 1989.	
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Alm		R. Kakkad et al., <i>Low Temperature Selective Crystallization of Amorphous Silicon</i> , Journal of Non-Crystalline Solids, Vol. 115, Pages 66-68, August 1, 1989.	
Alm		A.V. Dvurechenskii et al., <i>Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals</i> , Phys. Stat. Sol., Vol. 95, Pages 635-640, January 1, 1986.	
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Alm		E. Korin et al., <i>Crystallization of Amorphous Silicon Films Using a Multistep Thermal Annealing Process</i> , Thin Solid Films, Vol. 167, Pages 101-106, January 1, 1998	

Examiner Signature	<i>Alm</i>	Date Considered	6/12/2004
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